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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	39
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 13x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f031c6t6

Contents

List of figures

1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32F031x4/x6 microcontrollers.

This document should be read in conjunction with the STM32F0xxxx reference manual (RM0091). The reference manual is available from the STMicroelectronics website *www.st.com*.

For information on the ARM® Cortex®-M0 core, please refer to the Cortex®-M0 Technical Reference Manual, available from the www.arm.com website.

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

3.10.1 Temperature sensor

The temperature sensor (TS) generates a voltage V_{SENSE} that varies linearly with temperature.

The temperature sensor is internally connected to the ADC_IN16 input channel which is used to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode.

Table 3. Temperature sensor calibration values

Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at a temperature of 30 °C (± 5 °C), V_{DDA}= 3.3 V (± 10 mV)	0x1FFF F7B8 - 0x1FFF F7B9
TS_CAL2	TS ADC raw data acquired at a temperature of 110 °C (± 5 °C), V_{DDA}= 3.3 V (± 10 mV)	0x1FFF F7C2 - 0x1FFF F7C3

3.10.2 Internal voltage reference (V_{REFINT})

The internal voltage reference (V_{REFINT}) provides a stable (bandgap) voltage output for the ADC. V_{REFINT} is internally connected to the ADC_IN17 input channel. The precise voltage of V_{REFINT} is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode.

Table 4. Internal voltage reference calibration values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at a temperature of 30 °C (± 5 °C), V_{DDA}= 3.3 V (± 10 mV)	0x1FFF F7BA - 0x1FFF F7BB

3.10.3 V_{BAT} battery voltage monitoring

This embedded hardware feature allows the application to measure the V_{BAT} battery voltage using the internal ADC channel ADC_IN18. As the V_{BAT} voltage may be higher than V_{DDA}, and thus outside the ADC input range, the V_{BAT} pin is internally connected to a bridge divider by 2. As a consequence, the converted digital value is half the V_{BAT} voltage.

Figure 5. UFQFPN32 package pinout

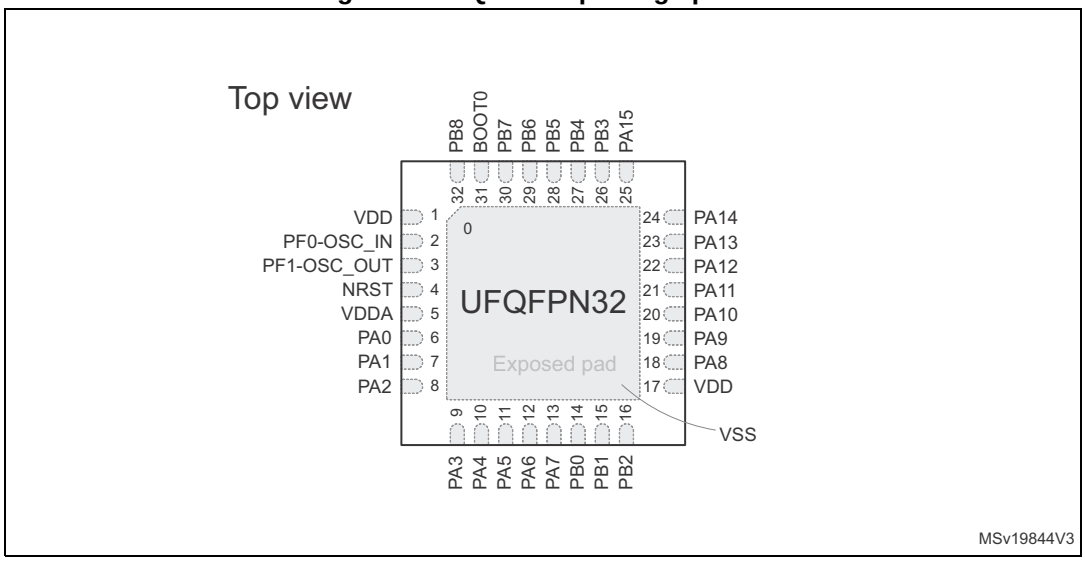


Figure 6. UFQFPN28 package pinout

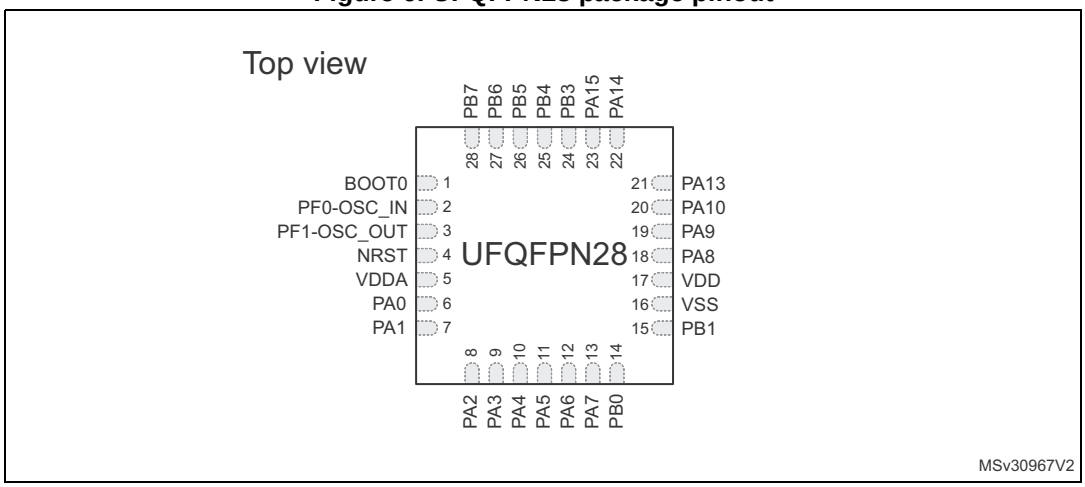


Table 11. Pin definitions (continued)

Pin number						Pin name (function upon reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP48	LQFP32	UFQFPN32	UFQFPN28	WLCSP25	TSSOP20					Alternate functions	Additional functions
6	3	3	3	B5	3	PF1-OSC_OUT (PF1)	I/O	FT	-	-	OSC_OUT
7	4	4	4	C5	4	NRST	I/O	RST	-	Device reset input / internal reset output (active low)	
8	16 (3)	0(3)	16 (3)	E1 (3)	15 (3)	VSSA	S		-	Analog ground	
9	5	5	5	D5	5	VDDA	S		-	Analog power supply	
10	6	6	6	B4	6	PA0	I/O	TTa	-	TIM2_CH1_ETR, USART1_CTS	ADC_IN0, RTC_TAMP2, WKUP1
11	7	7	7	C4	7	PA1	I/O	TTa	-	TIM2_CH2, EVENTOUT, USART1_RTS	ADC_IN1
12	8	8	8	D4	8	PA2	I/O	TTa	-	TIM2_CH3, USART1_TX	ADC_IN2
13	9	9	9	E5	9	PA3	I/O	TTa	-	TIM2_CH4, USART1_RX	ADC_IN3
14	10	10	10	B3	10	PA4	I/O	TTa	-	SPI1_NSS, I2S1_WS, TIM14_CH1, USART1_CK	ADC_IN4
15	11	11	11	C3	11	PA5	I/O	TTa	-	SPI1_SCK, I2S1_CK, TIM2_CH1_ETR	ADC_IN5
16	12	12	12	D3	12	PA6	I/O	TTa	-	SPI1_MISO, I2S1_MCK, TIM3_CH1, TIM1_BKIN, TIM16_CH1, EVENTOUT	ADC_IN6

Table 21. Programmable voltage detector characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD6}	PVD threshold 6	Rising edge	2.66	2.78	2.9	V
		Falling edge	2.56	2.68	2.8	V
V_{PVD7}	PVD threshold 7	Rising edge	2.76	2.88	3	V
		Falling edge	2.66	2.78	2.9	V
$V_{PVDhyst}$(1)	PVD hysteresis	-	-	100	-	mV
$I_{DD(PVD)}$	PVD current consumption	-	-	0.15	0.26(1)	µA

1. Guaranteed by design, not tested in production.

6.3.4 Embedded reference voltage

The parameters given in *Table 22* are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 18: General operating conditions*.

Table 22. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	–40 °C < T_A < +105 °C	1.2	1.23	1.25	V
t_{START}	ADC_IN17 buffer startup time	-	-	-	10(1)	µs
$t_{S\_vrefint}$	ADC sampling time when reading the internal reference voltage	-	4(1)	-	-	µs
ΔV_{REFINT}	Internal reference voltage spread over the temperature range	V_{DDA} = 3 V	-	-	10(1)	mV
T_{Coeff}	Temperature coefficient	-	- 100(1)	-	100(1)	ppm/°C

1. Guaranteed by design, not tested in production.

6.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in *Figure 13: Current consumption measurement scheme*.

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to CoreMark code.

6.3.6 Wakeup time from low-power mode

The wakeup times given in *Table 30* are the latency between the event and the execution of the first user instruction. The device goes in low-power mode after the WFE (Wait For Event) instruction, in the case of a WFI (Wait For Interruption) instruction, 16 CPU cycles must be added to the following timings due to the interrupt latency in the Cortex M0 architecture.

The SYSCLK clock source setting is kept unchanged after wakeup from Sleep mode. During wakeup from Stop or Standby mode, SYSCLK takes the default setting: HSI 8 MHz.

The wakeup source from Sleep and Stop mode is an EXTI line configured in event mode. The wakeup source from Standby mode is the WKUP1 pin (PA0).

All timings are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 18: General operating conditions*..

Table 30. Low-power mode wakeup timings

Symbol	Parameter	Conditions	Typ @V_{DD} = V_{DDA}					Max	Unit
			= 2.0 V	= 2.4 V	= 2.7 V	= 3 V	= 3.3 V		
t_{WUSTOP}	Wakeup from Stop mode	Regulator in run mode	3.2	3.1	2.9	2.9	2.8	5	µs
		Regulator in low power mode	7.0	5.8	5.2	4.9	4.6	9	
$t_{WUSTANDBY}$	Wakeup from Standby mode	-	60.4	55.6	53.5	52	51	-	
$t_{WUSLEEP}$	Wakeup from Sleep mode	-	4 SYSCLK cycles					-	

6.3.7 External clock source characteristics

High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO.

The external clock signal has to respect the I/O characteristics in *Section 6.3.14*. However, the recommended clock input waveform is shown in *Figure 14: High-speed external clock source AC timing diagram*.

Table 31. High-speed external user clock characteristics

Symbol	Parameter(1)	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency	-	8	32	MHz
V_{HSEH}	OSC_IN input pin high level voltage	0.7 V_{DDIOx}	-	V_{DDIOx}	V
V_{HSEL}	OSC_IN input pin low level voltage	V_{SS}	-	0.3 V_{DDIOx}	
$t_{w(HSEH)}$ $t_{w(HSEL)}$	OSC_IN high or low time	15	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time	-	-	20	

High-speed internal 14 MHz (HSI14) RC oscillator (dedicated to ADC)

Table 36. HSI14 oscillator characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI14}	Frequency	-	-	14	-	MHz
TRIM	HSI14 user-trimming step	-	-	-	1(2)	%
$DuCy_{(HSI14)}$	Duty cycle	-	45(2)	-	55(2)	%
ACC_{HSI14}	Accuracy of the HSI14 oscillator (factory calibrated)	T_A = –40 to 105 °C	–4.2(3)	-	5.1(3)	%
		T_A = –10 to 85 °C	–3.2(3)	-	3.1(3)	%
		T_A = 0 to 70 °C	–2.5(3)	-	2.3(3)	%
		T_A = 25 °C	–1	-	1	%
$t_{su(HSI14)}$	HSI14 oscillator startup time	-	1(2)	-	2(2)	µs
$I_{DDA(HSI14)}$	HSI14 oscillator power consumption	-	-	100	150(2)	µA

1. V_{DDA} = 3.3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by design, not tested in production.
3. Data based on characterization results, not tested in production.

Figure 19. HSI14 oscillator accuracy characterization results

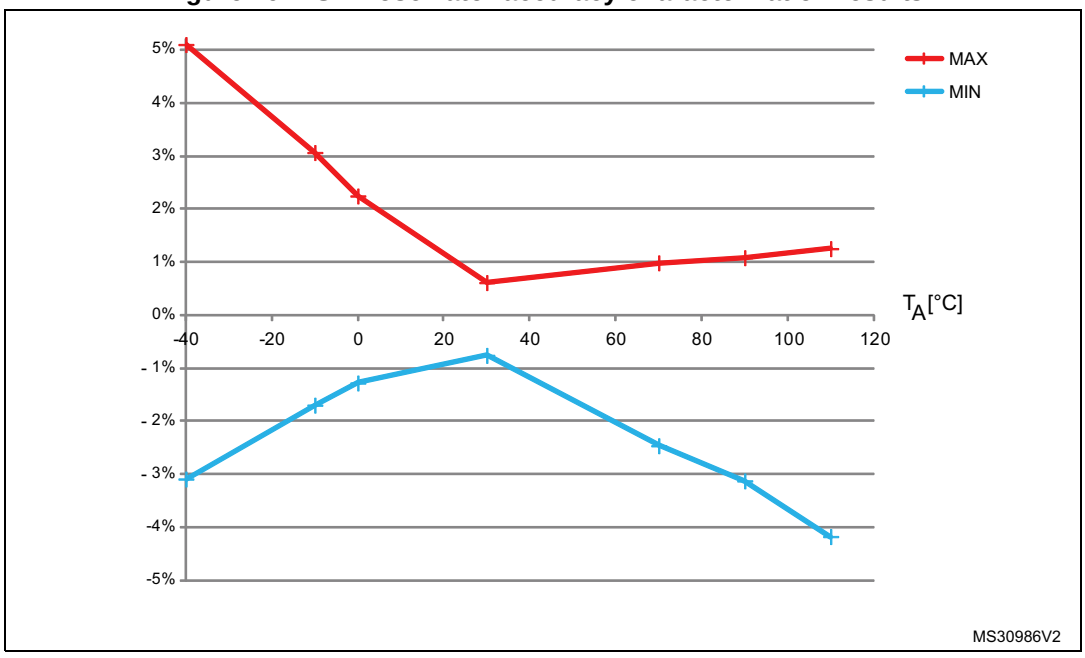


Table 43. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Packages	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C, conforming to JESD22-A114	All	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C, conforming to ANSI/ESD STM5.3.1	All	C3	250	V

1. Data based on characterization results, not tested in production.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 44. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = +105 °C conforming to JESD78A	II level A

6.3.13 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DDIOx} (for standard, 3.3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of the -5 µA/+0 µA range) or other functional failure (for example reset occurrence or oscillator frequency deviation).

The characterization results are given in *Table 45*.

Negative induced leakage current is caused by negative injection and positive induced leakage current is caused by positive injection.

Figure 20. TC and TTa I/O input characteristics

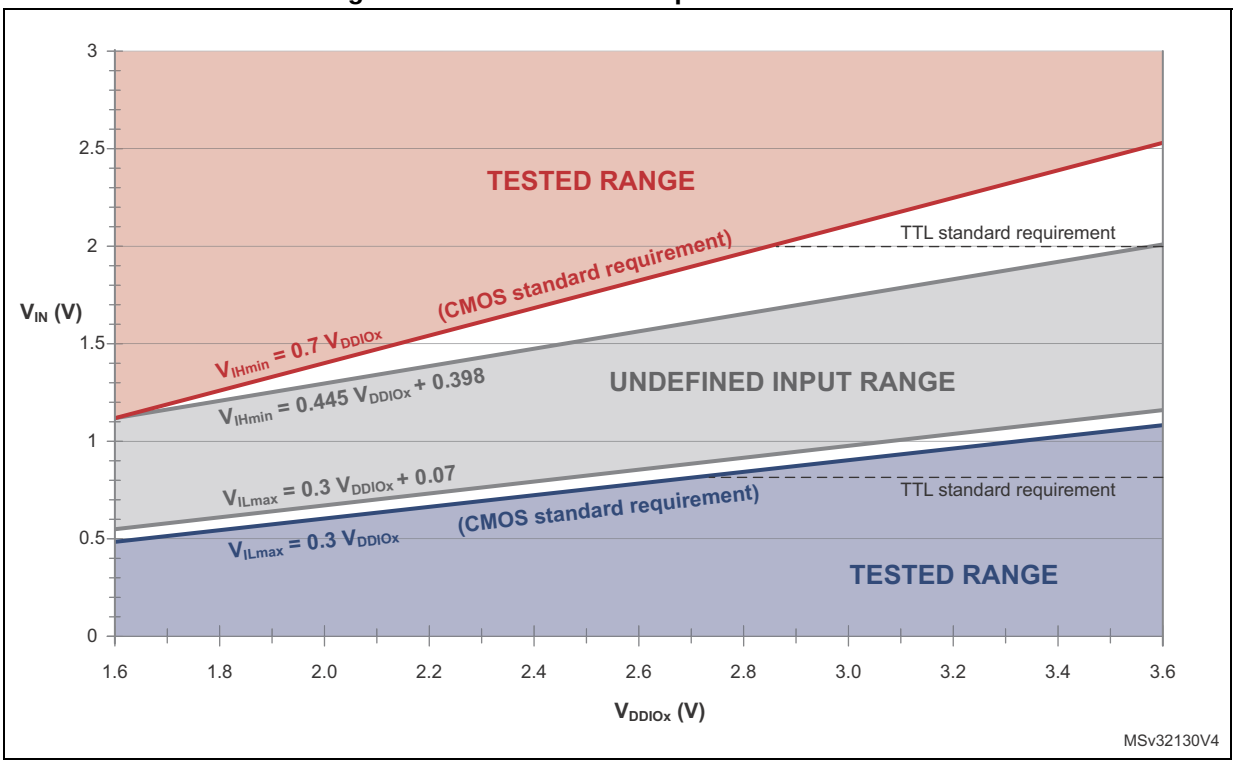


Figure 21. Five volt tolerant (FT and FTf) I/O input characteristics

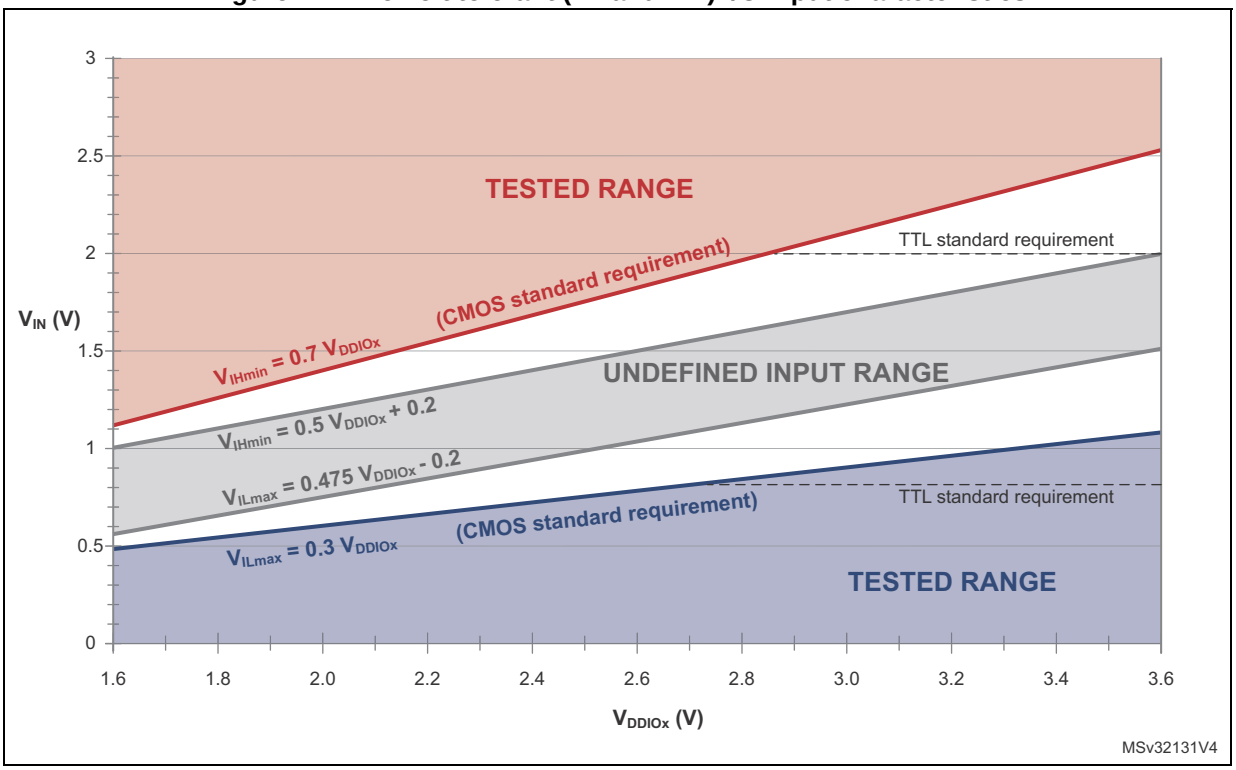


Table 58. I²C analog filter characteristics(1)

Symbol	Parameter	Min	Max	Unit
t_{AF}	Maximum width of spikes that are suppressed by the analog filter	50(2)	260(3)	ns

1. Guaranteed by design, not tested in production.
2. Spikes with widths below $t_{AF(min)}$ are filtered.
3. Spikes with widths above $t_{AF(max)}$ are not filtered

SPI/I²S characteristics

Unless otherwise specified, the parameters given in *Table 59* for SPI or in *Table 60* for I²S are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and supply voltage conditions summarized in *Table 18: General operating conditions*.

Refer to *Section 6.3.14: I/O port characteristics* for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI and WS, CK, SD for I²S).

Table 59. SPI characteristics(1)

Symbol	Parameter	Conditions	Min	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	18	MHz
		Slave mode	-	18	
$t_{r(SCK)}$ $t_{f(SCK)}$	SPI clock rise and fall time	Capacitive load: C = 15 pF	-	6	ns
$t_{su(NSS)}$	NSS setup time	Slave mode	4Tpclk	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode	2Tpclk + 10	-	
$t_{w(SCKH)}$ $t_{w(SCKL)}$	SCK high and low time	Master mode, f_{PCLK} = 36 MHz, presc = 4	Tpclk/2 -2	Tpclk/2 + 1	
$t_{su(MI)}$ $t_{su(SI)}$	Data input setup time	Master mode	4	-	
		Slave mode	5	-	
$t_{h(MI)}$	Data input hold time	Master mode	4	-	
$t_{h(SI)}$		Slave mode	5	-	
$t_{a(SO)}$(2)	Data output access time	Slave mode, f_{PCLK} = 20 MHz	0	3Tpclk	
$t_{dis(SO)}$(3)	Data output disable time	Slave mode	0	18	
$t_{v(SO)}$	Data output valid time	Slave mode (after enable edge)	-	22.5	
$t_{v(MO)}$	Data output valid time	Master mode (after enable edge)	-	6	
$t_{h(SO)}$	Data output hold time	Slave mode (after enable edge)	11.5	-	
$t_{h(MO)}$		Master mode (after enable edge)	2	-	
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	25	75	%

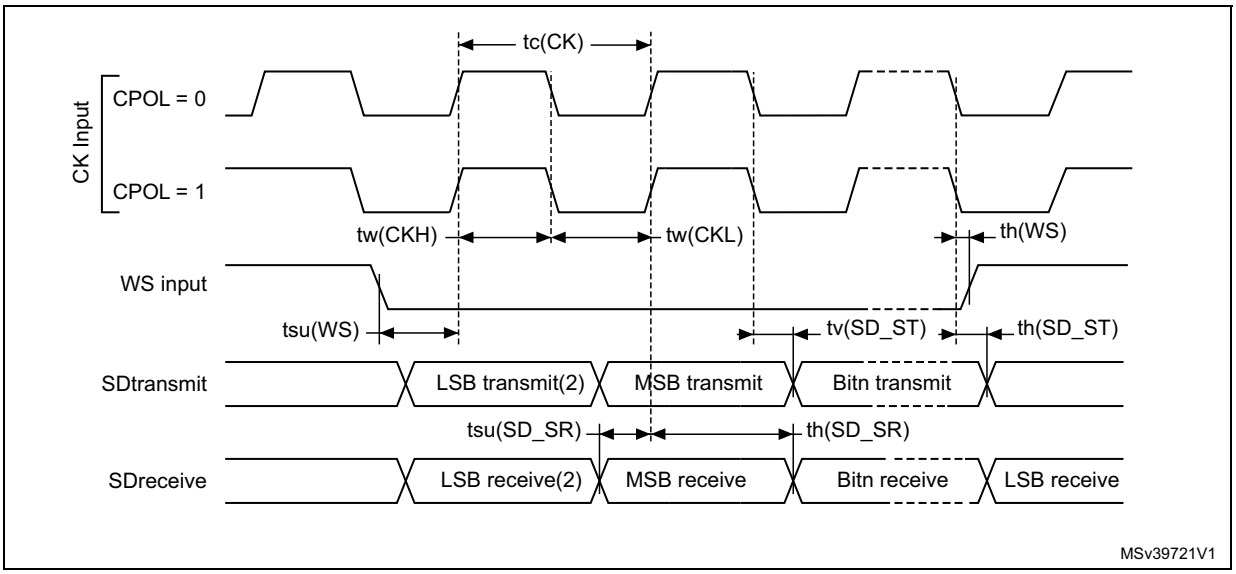
1. Data based on characterization results, not tested in production.
2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z

Table 60. I²S characteristics(1) (continued)

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{su(SD\_MR)}$	Data input setup time	Master receiver	6	-	ns
$t_{su(SD\_SR)}$		Slave receiver	2	-	
$t_{h(SD\_MR)}$(2)	Data input hold time	Master receiver	4	-	
$t_{h(SD\_SR)}$(2)		Slave receiver	0.5	-	
$t_{v(SD\_MT)}$(2)	Data output valid time	Master transmitter	-	4	
$t_{v(SD\_ST)}$(2)		Slave transmitter	-	20	
$t_{h(SD\_MT)}$	Data output hold time	Master transmitter	0	-	
$t_{h(SD\_ST)}$		Slave transmitter	13	-	

1. Data based on design simulation and/or characterization results, not tested in production.
2. Depends on f_{PCLK}. For example, if f_{PCLK} = 8 MHz, then T_{PCLK} = 1/f_{PLCLK} = 125 ns.

Figure 29. I²S slave timing diagram (Philips protocol)



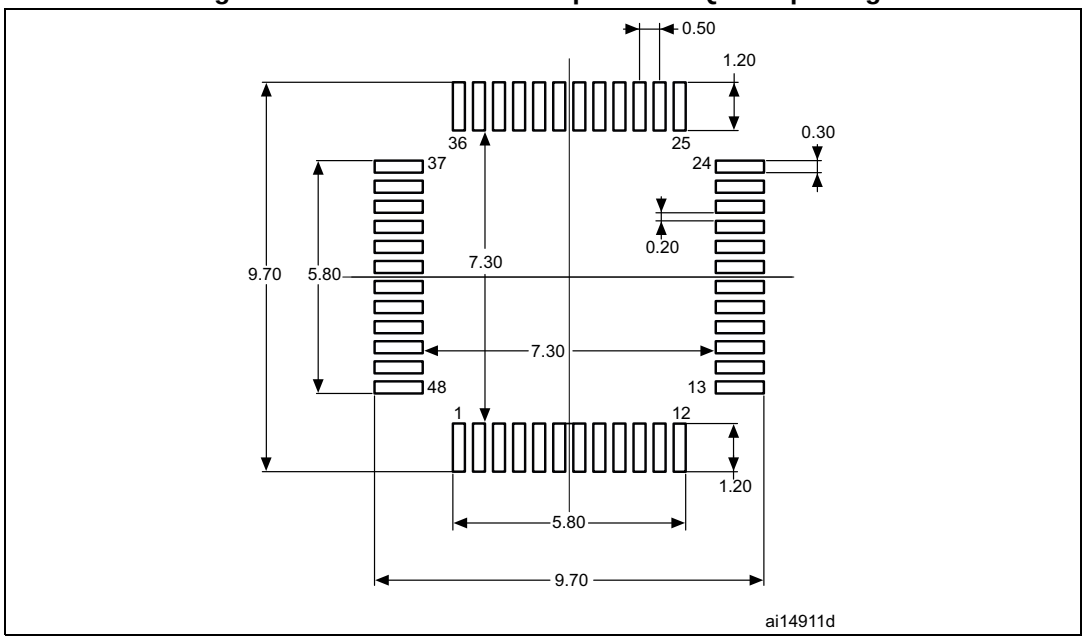
1. Measurement points are done at CMOS levels: 0.3 × V_{DDIOx} and 0.7 × V_{DDIOx}.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Table 61. LQFP48 package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	8.800	9.000	9.200	0.3465	0.3543	0.3622
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835
D3	-	5.500	-	-	0.2165	-
E	8.800	9.000	9.200	0.3465	0.3543	0.3622
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835
E3	-	5.500	-	-	0.2165	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 32. Recommended footprint for LQFP48 package

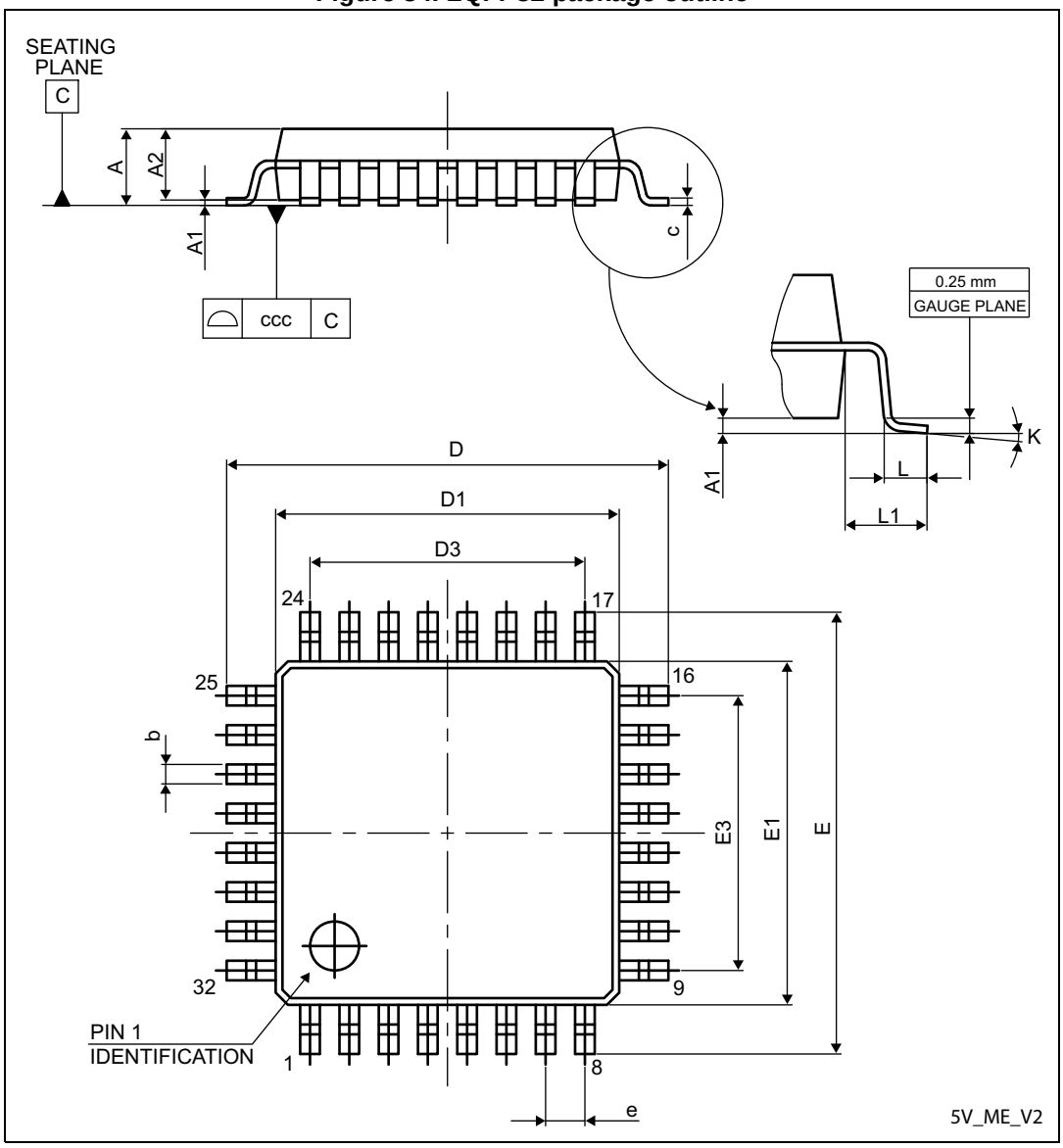


1. Dimensions are expressed in millimeters.

7.2 LQFP32 package information

LQFP32 is a 32-pin, 7 x 7 mm low-profile quad flat package.

Figure 34. LQFP32 package outline



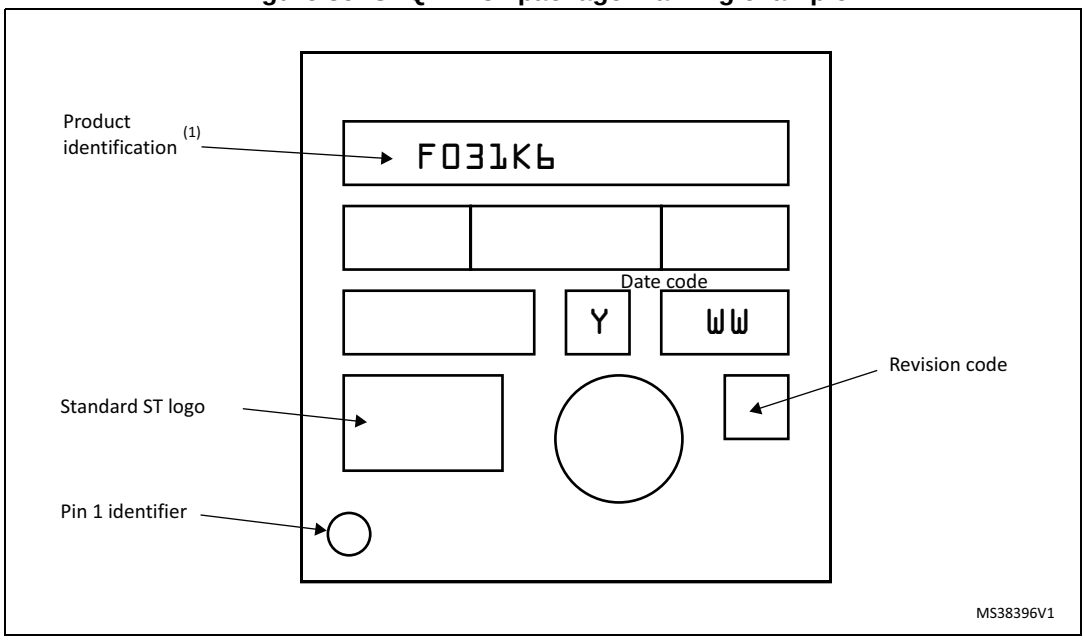
1. Drawing is not to scale.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 39. UFQFPN32 package marking example



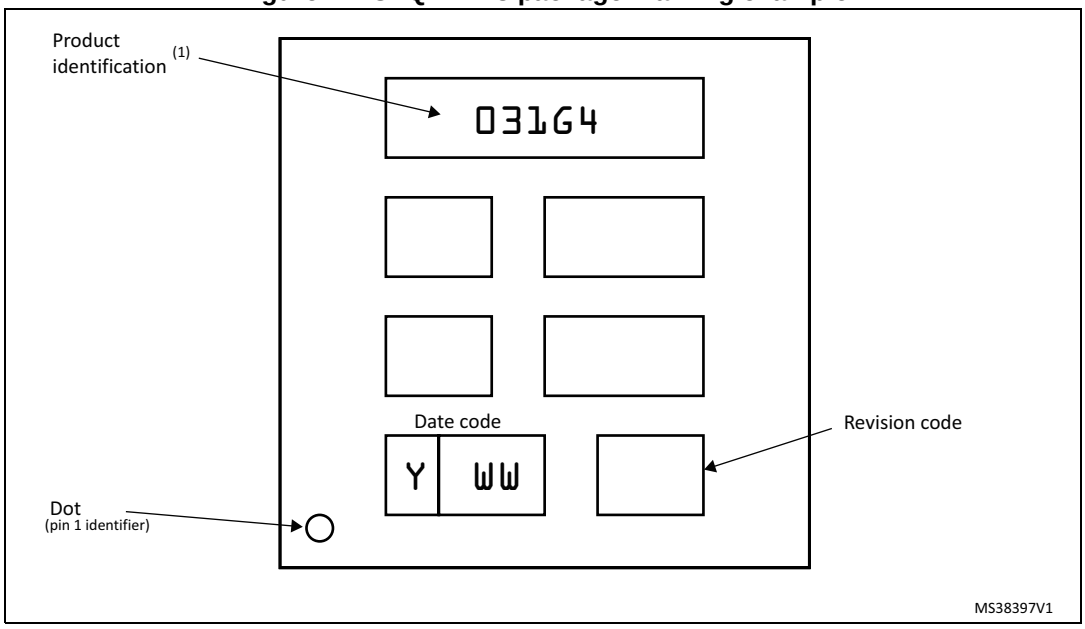
1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 42. UFQFPN28 package marking example



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Table 65. WLCSP25 package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
aaa	-	0.100	-	-	0.0039	-
bbb	-	0.100	-	-	0.0039	-
ccc	-	0.100	-	-	0.0039	-
ddd	-	0.050	-	-	0.0020	-
eee	-	0.050	-	-	0.0020	-

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Back side coating.
3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.
4. Primary datum Z and seating plane are defined by the spherical crowns of the bump.

Figure 44. Recommended footprint for WLCSP25 package

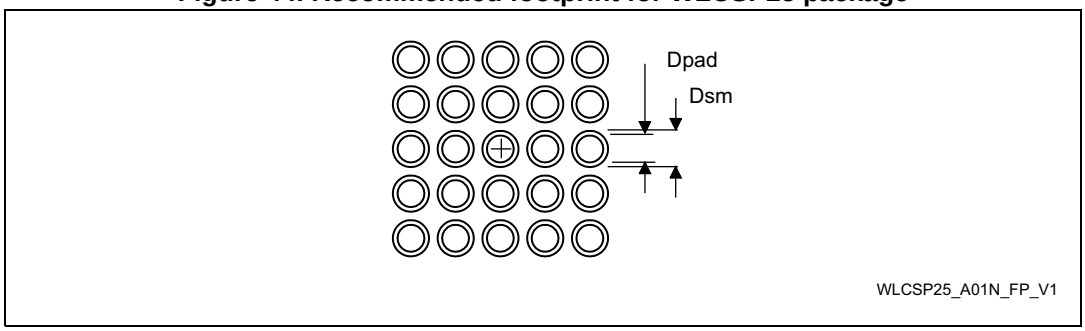


Table 66. WLCSP25 recommended PCB design rules

Dimension	Recommended values
Pitch	0.4 mm
Dpad	0.225 mm
Dsm	0.290 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.250 mm
Stencil thickness	0.100 mm

9 Revision history

Table 70. Document revision history

Date	Revision	Changes
13-Jan-2014	1	Initial release.
11-Jul-2014	2	Changed the document status to Datasheet - production data. Updated the following: – *Table: STM32F031x4/6 family device features and peripheral counts,* – *Figure: Clock tree*, – *Figure: Power supply scheme*, – *Table: Peripheral current consumption*. Replaced *Table Typical current consumption in Run mode, code with data processing running from Flash* and *Table Typical current consumption in Sleep mode, code running from Flash or RAM* with *Table: Typical current consumption, code executing from Flash, running from HSE 8 MHz crystal.* Added the LQFP32 package: updates in *Section: Description, Section: Pinouts and pin description* and *Section: Package information.*
28-Aug-2015	3	**Updated:** – *Figure 9: STM32F031x6 memory map* – AF1 alternate functions for PA0, PA1, PA2, PA3 and PA4 in *Table 12: Alternate functions selected through GPIOA_AFR registers for port A* – the footnote for V_{IN} max value in *Table 15: Voltage characteristics* – the footnote for max V_{IN} in *Table 18: General operating conditions* – *Table 22: Embedded internal reference voltage* with the addition of t_{START} parameter – *Table 50: ADC characteristics* – *Table 53: TS characteristics*: removed the min. value for t_{START} parameter – the typical value for R parameter in *Table 54: VBAT monitoring characteristics* – the structure of *Section 7: Package information*. **Added:** – *Figure 33: LQFP48 marking example (package top view), Figure 36: LQFP32 marking example (package top view), Figure 39: UFQFPN32 marking example (package top view), Figure 42: UFQFPN28 marking example (package top view), Figure 48: TSSOP20 marking example (package top view)*

Table 70. Document revision history (continued)

Date	Revision	Changes
16-Dec-2015	4 (continued)	– *Section 6.3.16: 12-bit ADC characteristics* - changed introductory sentence – *Table 60: I^2S characteristics*: table reorganized, $t_{v(SD\_ST)}$ max value updated ***Section 7: Package information*:** – *Figure 41: Recommended footprint for UFQFPN28 package* updated ***Section 8: Part numbering*:** – added tray packing to options
06-Jan-2017	5	***Section 6: Electrical characteristics*:** – *Table 34: LSE oscillator characteristics (f_{LSE} = 32.768 kHz)* - information on configuring different drive capabilities removed. See the corresponding reference manual. – *Table 22: Embedded internal reference voltage* - V_{REFINT} values – *Figure 26: SPI timing diagram - slave mode and CPHA = 0* and *Figure 27: SPI timing diagram - slave mode and CPHA = 1* enhanced and corrected ***Section 8: Ordering information*:** – The name of the section changed from the previous “Part numbering”